



NATIONAL INSTITUTE OF TECHNOLOGY, Rourkela

rage

EXPERIMENT NO - 5

- AIM OF THE EXPERIMENT -

To design a RC Coupled completion using MOSSET (Now are type) and collectate the parameters

- a) DC Condition
- to) Gain
- c) Frequency response and bondwith
- · APPARATUS REQUIRED -
- a Breadboard
- " CMD= 1C 4007
- c. De power Supply
- of Resistores
- e- Capacitons

· THEORY -

tised of all Moder amplifier strends A popular common source along with the signal ground trypess capacition and coupling capacition a shown in the figure. To determine the gain, we replace it with the cornesponding small signal model

* non the small signal model we can sont,

V - Vm (Km / Km + Km



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· DISCUSSION :-

- 1. The Common Source Configuration is the best suited for you obtaining the bulk of the gain required in an amplifien
- 2. Depending on the magnitude of the gain required Eithers a single CS stage on a cascade of two on three es stages can be used.
 - 3. A key step in the design of transistori amplifiers is to bias the transistor to operate at an appropriate point in the saturation region A good bias decign ensures that the parameters of the bias point ID . Vov and VDs are predictable and stable and do not vary by a large amount when the transistor is replaced by another of the same type.
 - 4. The internal Capacitances of the Mosfer cause the Mos amplifiers gain to fall off at high frequencies.
 - I Also, the coupling and bypass capacitons that are used in discrete Mos amplifiers cause the gain to fall off at low frequencies.
 - 6. The frequency band over which both sets of Capacitance can be neglected and hence over which the gain is constant, is known as midband.
 - The amplifier frequency response is characterized by the midband gain Am and the Lower and upper 3 de



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frequencies fr and fy respectively and the bandwidth is (ff + fr).

· PRECAUTIONS:

- . The input signal amphitude must be judiously chosen such that the amplified output should not enceed the De power supply otherwise the output will be elipped.
- . The De bias point should be preoperly fixed else the output would not be symmetrical to the input signal variation.

· CONICLUSION :-

The Cincuit was implemented and output determined for a very broad range of frequencies. The frequency response was plotted and the bandwidth was found to b. & ennon was about 0.7%.



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Observation table:

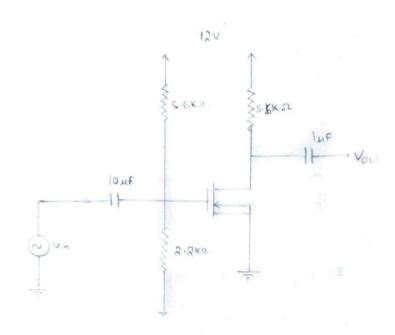
| | | | The state of the s | |
|-------|-----------|---------|--|------------------------------|
| Von | frequency | Voud | Gen (Vo/vin) | Gain in dB 20log (Vo/vin) |
| 100mV | 10 Hz | 108 mV | 1.08 | 0.66 dB |
| | 50 Hz | 464 mV | 4.64 | 13.33 48. |
| | 100 1/2 | 960 mV | 9.6 | 19.64 dB |
| | 500 Hz | 1 V | 10 | 20 |
| | L KH2 | 1. V | 10 | 20 |
| | 2KHz | lv | 10 | 20 |
| | SKH2 | 1 V | 10 | 2.0 |
| | 7KHz | 1 V | 10 | 20 |
| | 10 KHz | l V | 10 | 20 |
| | 20 KHz | IV | 10 | 20 |
| | 50 KH2 | 1 V | 10 | 20 |
| - / 2 | LOOKHZ | 920 mV | 9.2 | 19.275 |
| | 200 KHz | 728 mV | 7.28 | 17. 242 |
| | 500 KH2 | 400 mV | 4 | 12.041 |
| | IMHz. | 2 24 mV | a·24 | 7.60 |

Emperimental mid frequency Gain = 20 dB.

Theoritical Gam = 20.16 dB.

y. Fremon: 20.16 - 20 x 100 = 0.7 %.

Bandwidth : ft - ft





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Vsually Rq & selected very large (E.g & the Mir range) with the nexult that is many applications Rq >> Resy and

stownings et; The Supply was lav

Assyming y = 1.5 V.

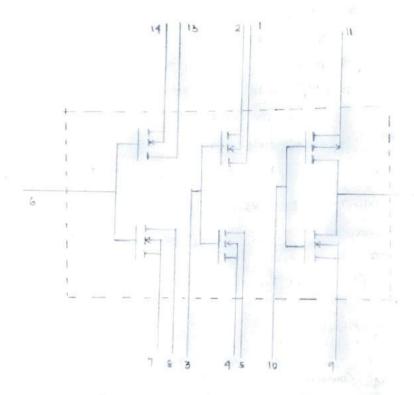
Thus, the "theoretical gam of the circuit was found to

the decibel the gam was found to be 20.16 dB.

· Tabulation -

starting frequency: 10 Hz.

Input Voltage Upk-pk 100 mV.



CMOS 104007 (INTERNAL STRUCTURE)



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Usually Rq is selected very large (e.g in the Msz range) with the result that in many applications Rq>> Rsig and

$$V_i \cong V_{sig}$$
Now, $V_{gs} = V_i$

Thus the voltage gain Av is

and the open-circuit voltage gain u

The overlass voltage gain from the signal-source to the load will be

The output nesistance is 8.11 RD.

. DESIGN OF CIRCUIT & CALCULATION -

The resistance and capacitance values were taken as given in the circuit diagram.

The die bias values were measured as follows.

Vp - 2.4 volt

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